

# FQPF47P06 / FQPF47P06YDTU

## P-Channel QFET® MOSFET

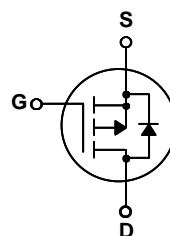
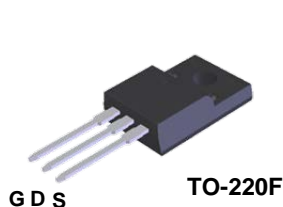
-60 V, -30 A, 26 mΩ

### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- -30 A, -60 V,  $R_{DS(on)}=26\text{ m}\Omega(\text{Max.}) @V_{GS}=-10\text{ V}, I_D=-15\text{ A}$
- Low Gate Charge (Typ. 84 nC)
- Low Crss (Typ. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter   | FQPF47P06 / FQPF47P06YDTU | Unit                |
|----------------|---|---------------------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage  | -60                       | V                   |
| $I_D$          | Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )                       | -30                       | A                   |
|                | - Continuous ( $T_C = 100^\circ\text{C}$ )                                    | -21.2                     | A                   |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)   | -120                      | A                   |
| $V_{GSS}$      | Gate-Source Voltage   | $\pm 25$                  | V                   |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                                       | 820                       | mJ                  |
| $I_{AR}$       | Avalanche Current (Note 1)  | -30                       | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)  | 6.2                       | mJ                  |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note 3)  | -7.0                      | V/ns                |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )                                | 62                        | W                   |
|                | - Derate above $25^\circ\text{C}$   | 0.41                      | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                       | -55 to +175               | $^\circ\text{C}$    |
| $T_L$          | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 300                       | $^\circ\text{C}$    |

### Thermal Characteristics

| Symbol          | Parameter                               | Typ | Max  | Unit                      |
|-----------------|---|-----|------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case    | --  | 2.42 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | --  | 62.5 | $^\circ\text{C}/\text{W}$ |

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

**Off Characteristics**

|                                |   |  |     |       |      |                     |
|--------------------------------|---|--|-----|-------|------|---------------------|
| $BV_{DSS}$                     | Drain-Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$               | -60 | --    | --   | V                   |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$ | --  | -0.06 | --   | V/ $^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$                       | --  | --    | -1   | $\mu\text{A}$       |
|                                |   | $V_{DS} = -48\text{ V}, T_C = 150^\circ\text{C}$                   | --  | --    | -10  | $\mu\text{A}$       |
| $I_{GSSF}$                     | Gate-Body Leakage Current, Forward        | $V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$                       | --  | --    | -100 | nA                  |
| $I_{GSSR}$                     | Gate-Body Leakage Current, Reverse        | $V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$                        | --  | --    | 100  | nA                  |

**On Characteristics**

|              |                                   |  |      |       |       |          |
|--------------|-----------------------------------|--|------|-------|-------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$     | -2.0 | --    | -4.0  | V        |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = -10\text{ V}, I_D = -15\text{ A}$          | --   | 0.021 | 0.026 | $\Omega$ |
| $g_{FS}$     | Forward Transconductance          | $V_{DS} = -30\text{ V}, I_D = -15\text{ A}$ (Note 4) | --   | 19    | --    | S        |

**Dynamic Characteristics**

|           |                              |   |    |      |      |    |
|-----------|------------------------------|---|----|------|------|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$ | -- | 2800 | 3600 | pF |
| $C_{oss}$ | Output Capacitance           |   | -- | 1300 | 1700 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |   | -- | 320  | 420  | pF |

**Switching Characteristics**

|              |                     |   |    |     |     |    |
|--------------|---------------------|---|----|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = -30\text{ V}, I_D = -23.5\text{ A},$<br>$R_G = 25\text{ }\Omega$<br><br>(Note 4, 5) | -- | 50  | 110 | ns |
| $t_r$        | Turn-On Rise Time   |   | -- | 450 | 910 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |   | -- | 100 | 210 | ns |
| $t_f$        | Turn-Off Fall Time  |   | -- | 195 | 400 | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = -48\text{ V}, I_D = -47\text{ A},$<br>$V_{GS} = -10\text{ V}$<br><br>(Note 4, 5)    | -- | 84  | 110 | nC |
| $Q_{gs}$     | Gate-Source Charge  |   | -- | 18  | --  | nC |
| $Q_{gd}$     | Gate-Drain Charge   |   | -- | 44  | --  | nC |

**Drain-Source Diode Characteristics and Maximum Ratings**

|                 |   |  |    |      |      |    |
|-----------------|---|--|----|------|------|----|
| I <sub>S</sub>  | Maximum Continuous Drain-Source Diode Forward Current |  | -- | --   | -30  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain-Source Diode Forward Current     |  | -- | --   | -120 | A  |
| V <sub>SD</sub> | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = -30 A  | -- | --   | -4.0 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                 | V <sub>GS</sub> = 0 V, I <sub>S</sub> = -47 A, | -- | 130  | --   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                               | dI <sub>F</sub> / dt = 100 A/μs (Note 4)       | -- | 0.55 | --   | μC |

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 1.06\text{ mH}, I_{AS} = -30\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -47\text{ A}, dI/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

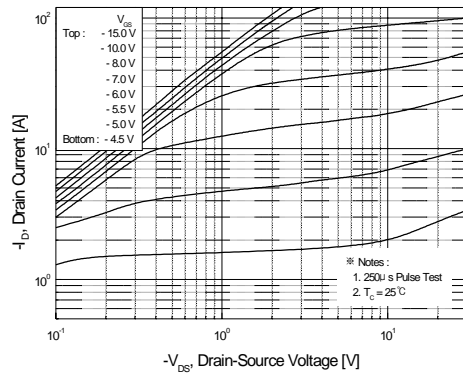


Figure 1. On-Region Characteristics

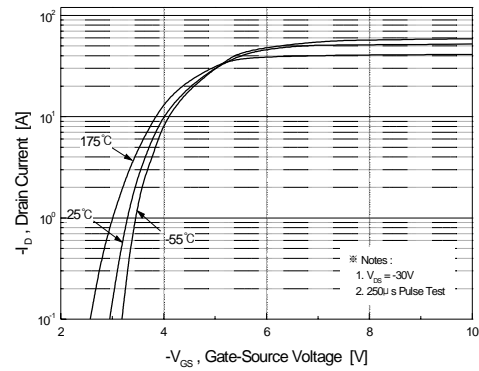


Figure 2. Transfer Characteristics

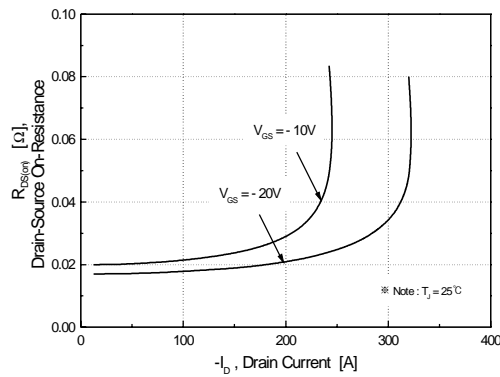


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

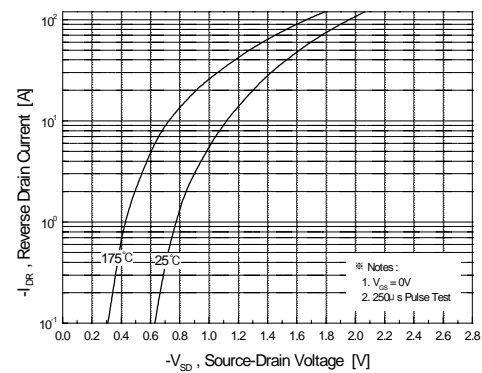


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

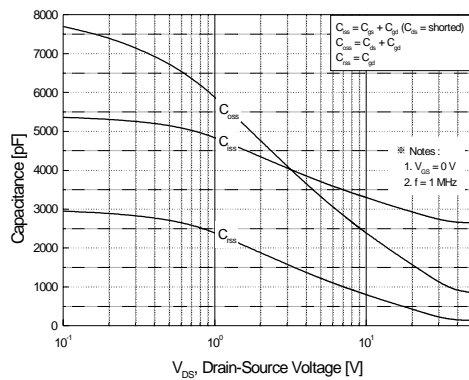


Figure 5. Capacitance Characteristics

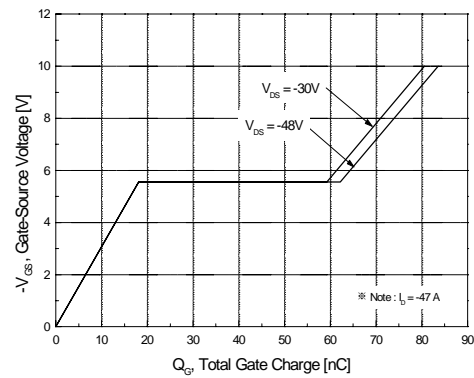


Figure 6. Gate Charge Characteristics

## Typical Characteristics (Continued)

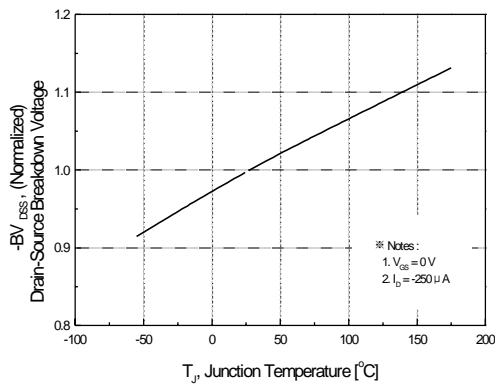


Figure 7. Breakdown Voltage Variation vs. Temperature

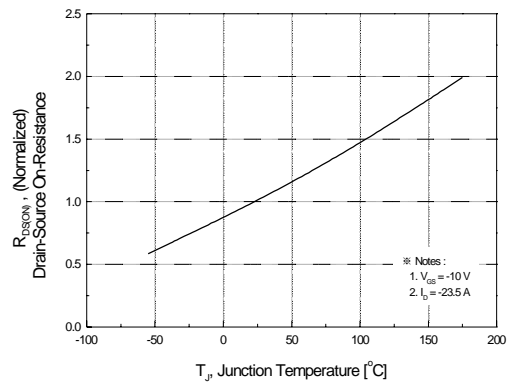


Figure 8. On-Resistance Variation vs. Temperature

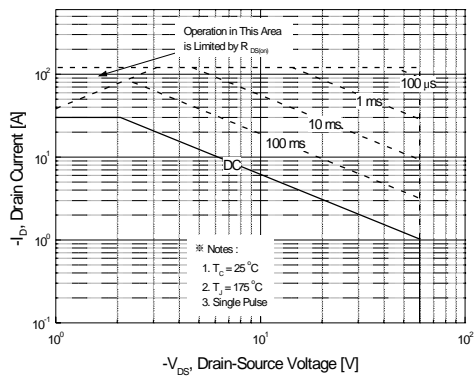


Figure 9. Maximum Safe Operating Area

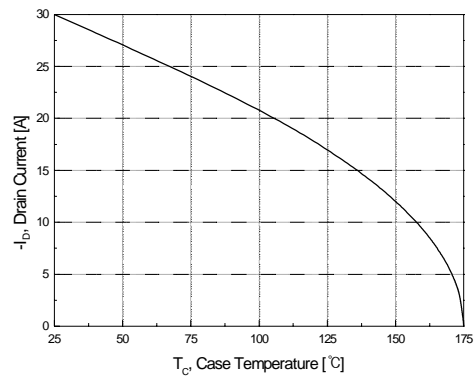


Figure 10. Maximum Drain Current vs. Case Temperature

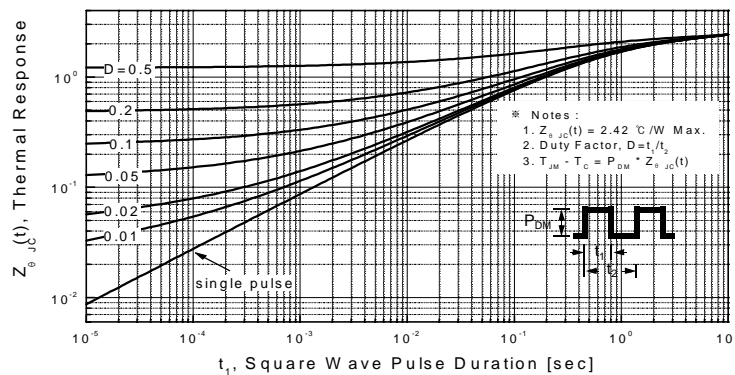
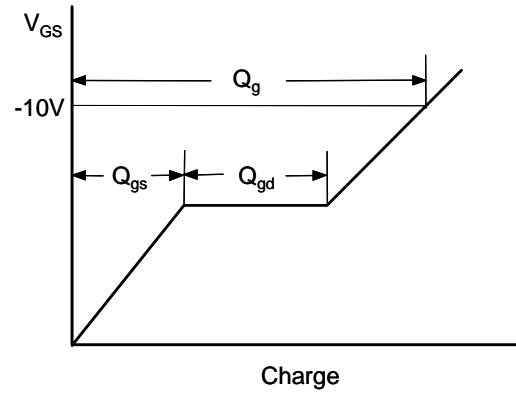
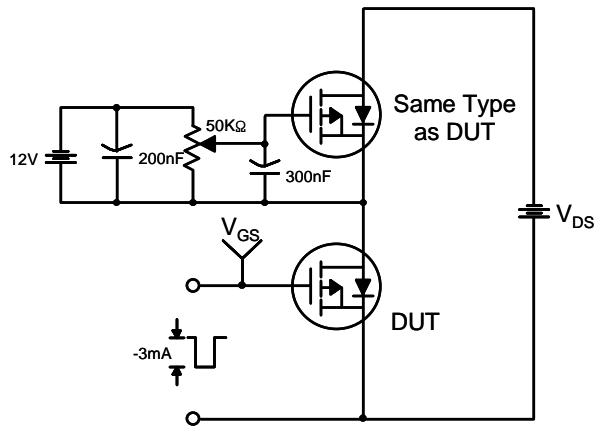
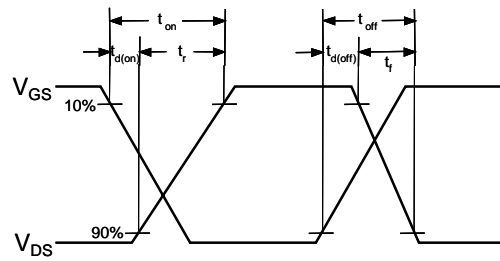
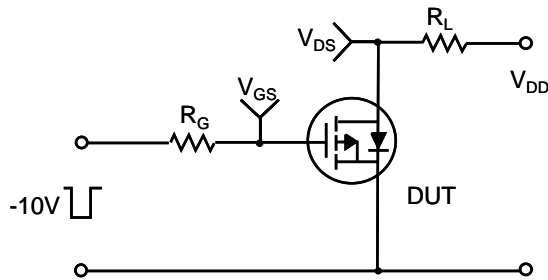


Figure 11. Transient Thermal Response Curve

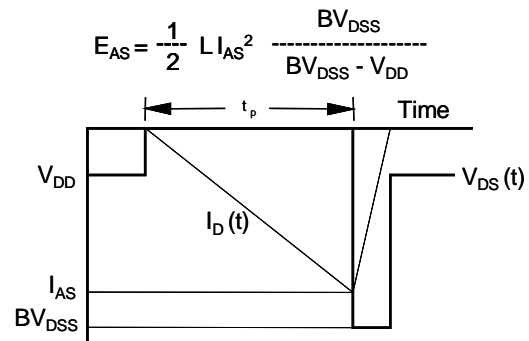
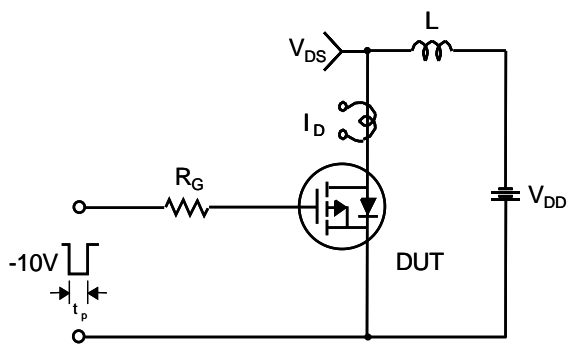
### Gate Charge Test Circuit & Waveform



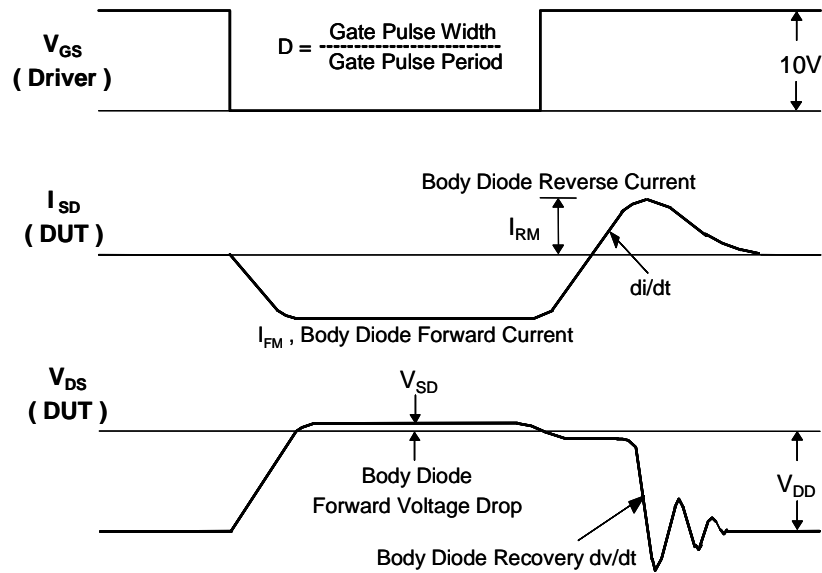
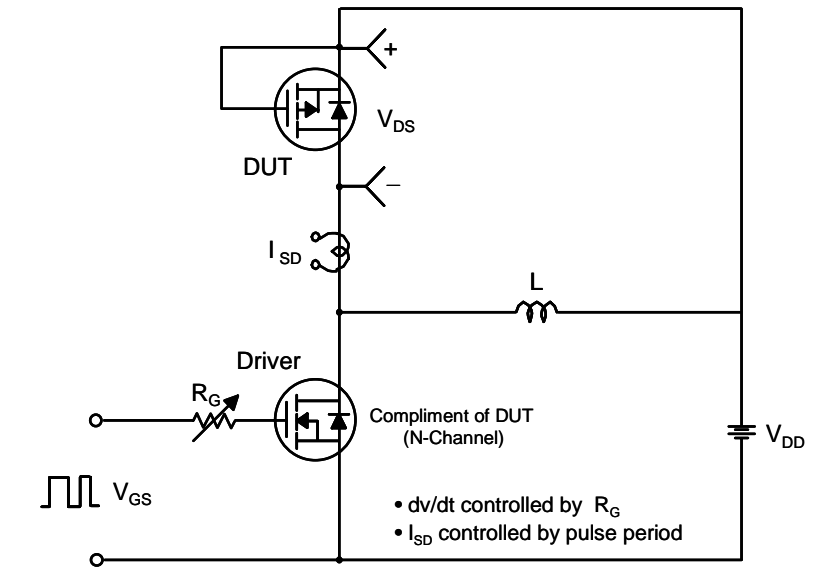
### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms

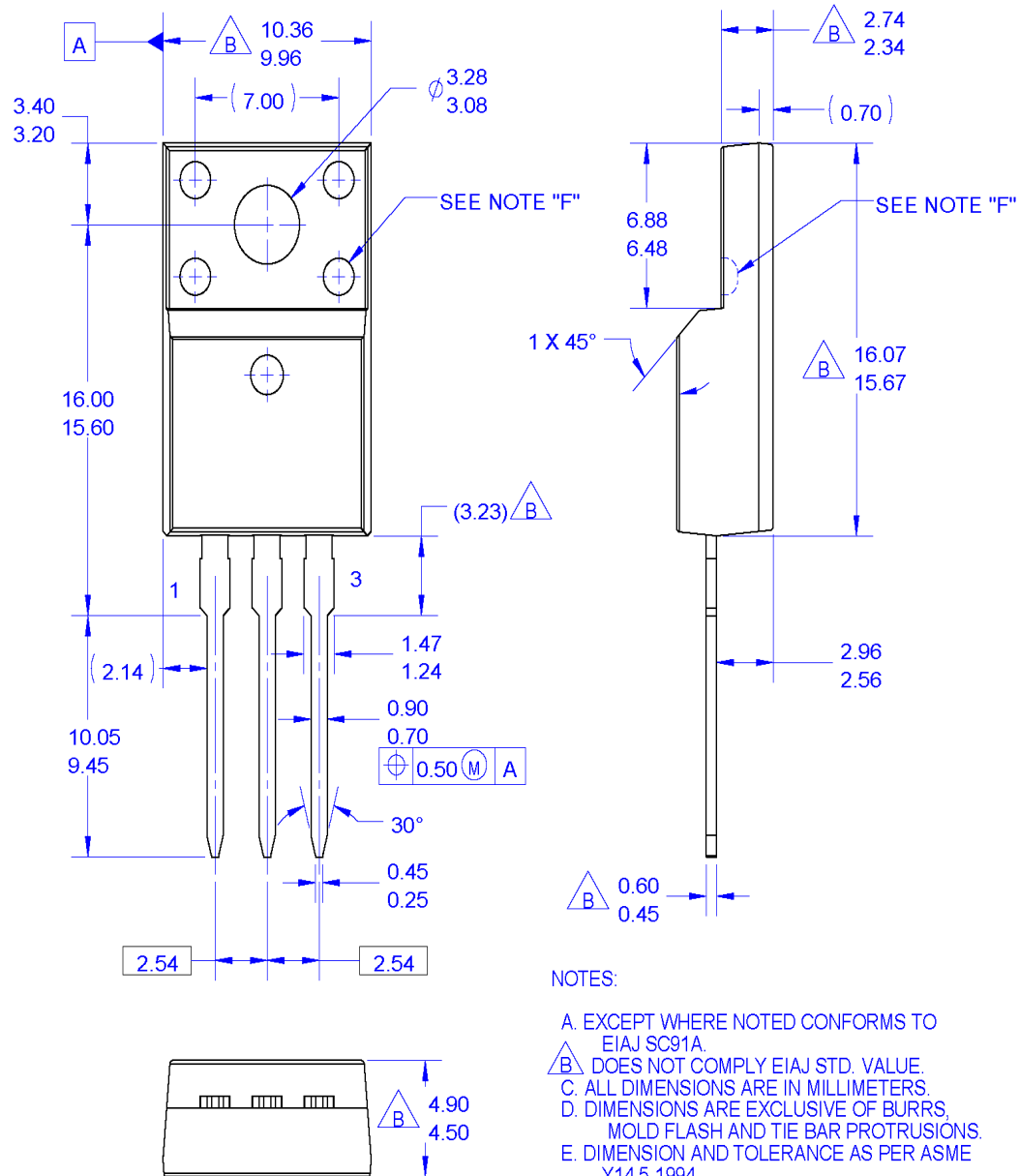


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions

# TO-220F



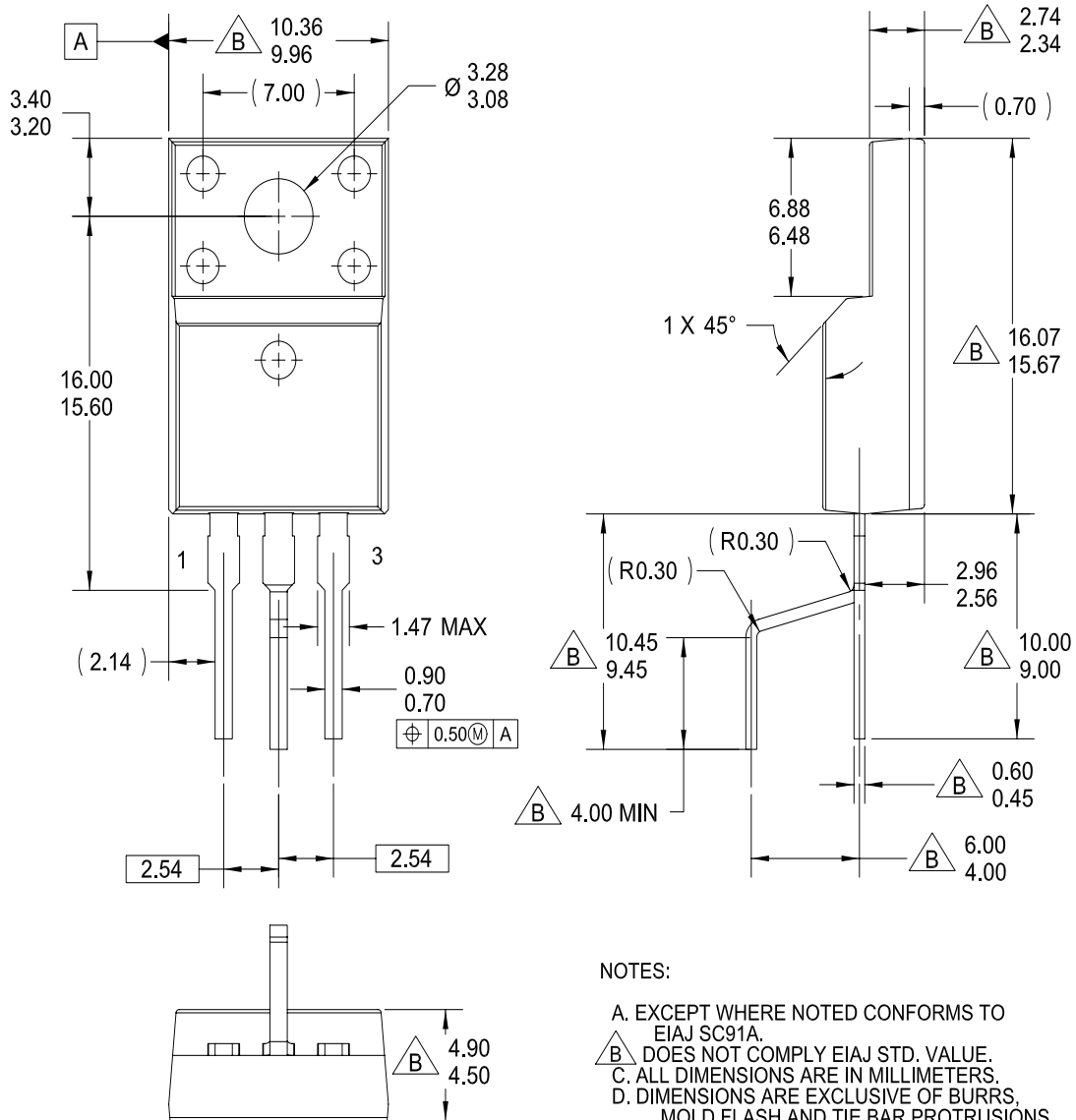
NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.**
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSIONS AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.  
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

### Dimensions in Millimeters

## Mechanical Dimensions

### TO-220F (Y-Forming)



#### NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. DRAWING FILE NAME: TO220Q03REV1

Dimensions in Millimeters





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